Amendments to the Claims:

This listing of claims will replace all prior version and listings of claims in the application:

Listing of Claims:

- 1. (Currently amended) A semiconductor device, comprising:
 - a trench formed in a substrate;
 - a diffusion region surrounding the trench to form a buried plate;
- a first conductive material formed in the trench, wherein the first conductive material comprises a <u>at least one</u> pillar extending from a bottom of the trench, wherein the first conductive material contacts the buried plate along an entire bottom portion of the trench and along a lower portion of the sidewalls of the trench, and wherein the first conductive material and the buried plate form a first electrode;
- a second conductive material disposed in the trench to form a second electrode; and
- a node dielectric layer formed between the first electrode and the second electrode.
- 2. (Currently amended) The semiconductor device as recited in claim 1, wherein the first conductive material is formed into comprises a plurality of pillars extending from the bottom of the trench.
- 3. (Currently amended) The semiconductor device as recited in claim 2, wherein the plurality of pillars includes a portion of the second conductive material is disposed between the plurality of pillars.
- 4. (Original) The semiconductor device as recited in claim 1, wherein the first conductive material includes one of a doped polysilicon and a doped amorphous silicon.

- 5. (Original) The semiconductor device as recited in claim 1, wherein the second conductive material includes doped amorphous silicon.
- 6. (Currently amended) The semiconductor device as recited in claim 1, wherein a portion of the second conductive material is disposed between the first conductive material and the buried plate.

7-17. (Canceled).

- (Currently amended) A semiconductor device, comprising:
 a trench formed in a substrate;
 - a diffusion region surrounding the trench to form a buried plate;
- a first conductive material formed in the trench, wherein the first conductive material comprises a pillar plurality of pillars extending from a bottom of the trench, wherein the first conductive material contacts the buried plate along an entire bottom portion of the trench and along a lower portion of the sidewalls of the trench, and wherein the first conductive material and the buried plate form a first electrode;
- a second conductive material disposed in the trench to form a second electrode; and
- a node dielectric layer formed between the first electrode and the second electrode.
- 19. (Currently amended) The semiconductor device as recited in claim 7 18, wherein the first conductive material is formed into a the plurality of pillars extending from the bottom of the trench.
- 20. (Currently amended) The semiconductor device as recited in claim 8 <u>19</u>, wherein the plurality of pillars includes the second conductive material disposed between the plurality of pillars.
- 21. (Currently amended) The semiconductor device as recited in claim 7 18, wherein the first conductive material includes one of a doped polysilicon and a doped amorphous silicon.

- 22. (Currently amended) The semiconductor device as recited in claim 7 18, wherein the second conductive material includes doped amorphous silicon.
- 23. (Currently amended) The semiconductor device as recited in claim 7 18, wherein the second conductive material is disposed between the first conductive material and the buried plate.